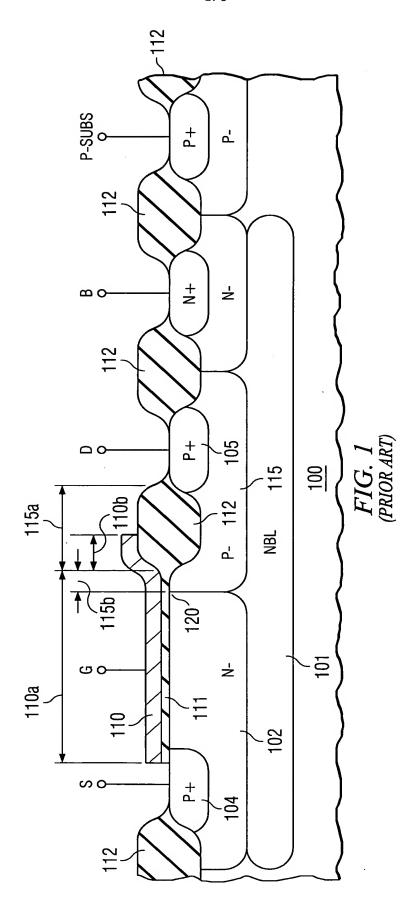
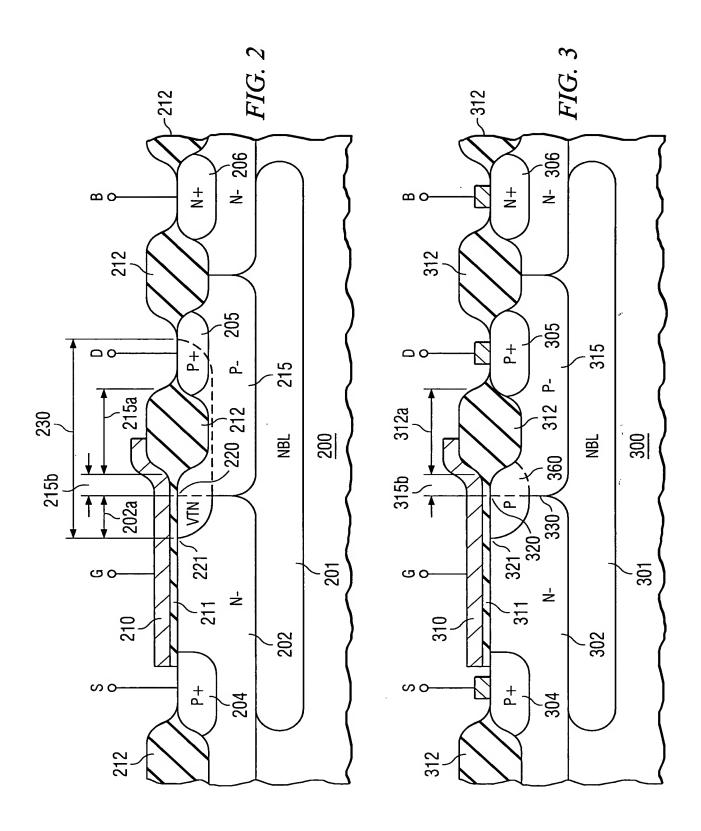
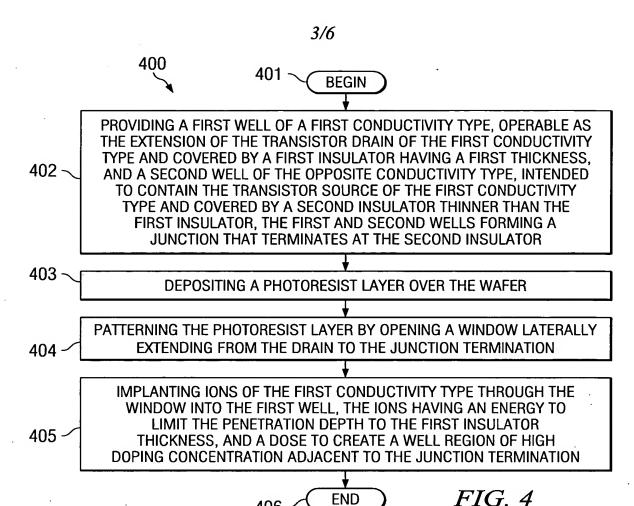
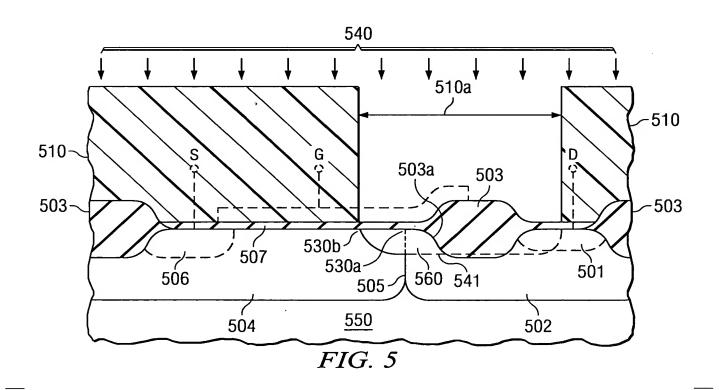


1/6









**END** 

406 -

4/6 600 601 -**BEGIN** 602 ~ PROVIDING A SEMICONDUCTOR WAFER OF A FIRST CONDUCTIVITY TYPE 603 FORMING A BURIED LAYER OF THE OPPOSITE CONDUCTIVITY TYPE 604 FORMING A FIRST WELL OF OPPOSITE CONDUCTIVITY TYPE 605 FORMING A SECOND WELL OF THE FIRST CONDUCTIVITY TYPE 606 FORMING A FIRST (THICK) INSULATOR LAYER FORMING A SECOND (THIN) INSULATOR OVER ACTIVE REGIONS, PROTECTING 607 -THE JUNCTION END POINT BETWEEN THE FIRST AND SECOND WELL 608 **DEPOSITING PHOTORESIST LAYER OPENING WINDOW IN PHOTORESIST LAYER** 609 FROM DRAIN REGION TO JUNCTION END POINT IMPLANTING IONS OF FIRST CONDUCTIVITY 610 TYPE THROUGH THE PHOTORESIST WINDOW REMOVING THE PHOTORESIST LAYER 611 REMOVING FIRST INSULATING LAYER 612 FORMING THE GATE INSULATOR LAYER 613 FORMING THE POLYSILICON LAYER 614 FORMING THE SOURCE AND DRAIN REGIONS 615-FORMING SILICIDE, INTERLAYER DIELECTRIC, CONTACTS, 616 METALLIZATION, PASSIVATION, AND OTHER "BACK END" PROCESSES 617 -

FIG. 6

